



20V N-CHANNEL ENHANCEMENT MODE MOSFET

Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2) Halogen and Antimony Free. "Green" Device (Note 3) Qualified to AEC-Q101 Standards for High Reliability

Product Summary

V _{(BR)DSS}	R _{DS(ON)}	I _D T _A = +25℃
	0.200Ω @ V _{GS} =4.5V	2.1A
20V	0.240Ω @ V _{GS} =2.5V	1.9A
	0.310Ω @ V _{GS} =1.8V	1.7A

Description

This MOSFET is designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

- Power Management Functions
- Disconnect Switches
- Relay Driving and Load Switching

SOT26



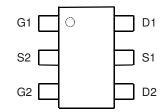


Mechanical Data Case: SOT26

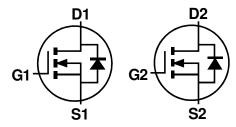
Features and Benefits
Low On-Resistance
Low Gate Drive Capability
SOT26 (dual) Package

- Case: SO126
- Case Material: Molded Plastic.

 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (23)
- Weight: 0.018 grams (Approximate)



Pin Out - Top View



Equivalent Circuit

Ordering Information (Note 4)

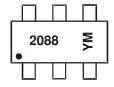
Part Number	Compliance	Case	Packaging
ZXMN2088DE6TA	Standard	SOT26	3,000 / Tape & Reel
ZXMN2088DE6TC	Standard	SOT26	10,000 / Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

SOT26



 $\begin{array}{l} 2088 = Product\ Type\ Marking\ Code \\ YM = Date\ Code\ Marking \\ Y\ or\ \overline{Y} = Year\ (ex:\ C=2015) \\ M\ or\ \overline{M} = Month\ (ex:\ 9=September) \end{array}$

Date Code Key

Year	2015		2016	2017		2018	2019		2020	2021		2022
Code	С		D	Е		F	G		Н			J
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage	Drain-Source Voltage			20	V
Gate-Source Voltage			V_{GS}	±8	V
		T _A = +25 °C (Notes 6 & 8)		2.1	
Continuous Drain Current V _{GS} =	$V_{GS} = 4.5V$	T _A = +70°C (Notes 6 & 8)	I_{D}	1.7	Α
		T _A = +25°C (Notes 5 & 8)		1.7	
Pulsed Drain Current (Note 7)			I _{DM}	8	Α

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
	(Notes 5 & 8)	P _D	0.9 7.2	W mW/°C
Power Dissipation at T _A = +25℃ Linear Derating Factor	(Notes 5 & 9)	P _D	1.1 8.8	W mW/℃
	(Notes 6 & 8)	P _D	1.3 10.4	W mW/°C
	(Notes 5 & 8)		139	
Thermal Resistance, Junction to Ambient	(Notes 5 & 9)	R _{0JA}	113	°C/W
	(Notes 6 & 8)		96	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	∞

Notes:

^{5.} For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.

^{6.} Same as Note (5), except the device is measured at $t \le 5$ sec.

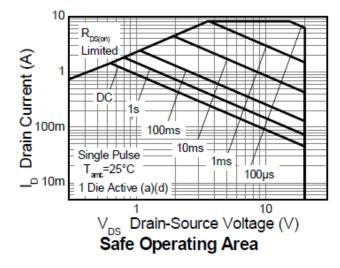
^{7.} Same as Note (5), except the device is pulsed with D = 0.02 and pulse width 300µs. The pulse width is limited by the maximum junction temperature.

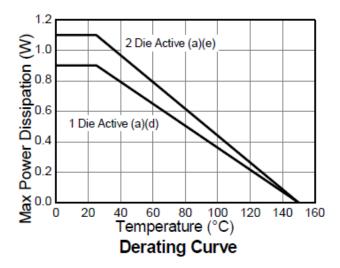
^{8.} For device with one active die.

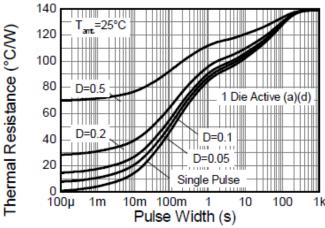
^{9.} For device with two active die running at equal power.

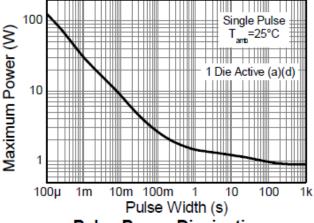


Thermal Characteristics









Transient Thermal Impedance

Pulse Power Dissipation



Electrical Characteristics (@T_A = +25 °C, unless otherwise specified.)

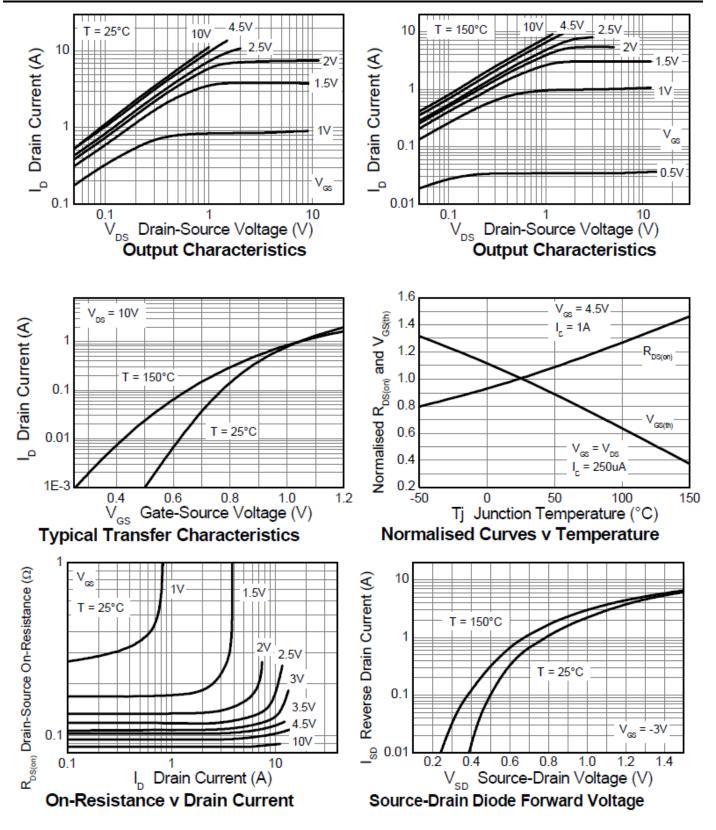
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	20	_	_	٧	$I_D = 250 \mu A, V_{GS} = 0 V$
Zero Gate Voltage Drain Current	I _{DSS}		_	100	nA	$V_{DS} = 3V$, $V_{GS} = 0V$
Zero Gate Voltage Drain Current	I _{DSS}		_	1	μΑ	$V_{DS} = 20V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}		_	±100	nA	$V_{GS} = \pm 8V$, $V_{DS} = 0V$
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(th)}$	0.4	_	1.0	٧	$I_D=250\mu A,\ V_{DS}=V_{GS}$
			0.112	0.200		$V_{GS} = 4.5V, I_D = 1.0A$
Static Drain-Source On-Resistance (Note 10)	R _{DS(ON)}	_	0.137	0.240	Ω	$V_{GS} = 2.5V, I_D = 0.6A$
			0.165	0.310		$V_{GS} = 1.8V, I_D = 0.3A$
Forward Transconductance (Notes 10 & 12)	g _{fs}		4.6	_	S	$V_{DS} = 10V, I_D = 1.0A$
Diode Forward Voltage (Note 12)	V_{SD}	_	0.75	0.95	V	$I_S = 1.0A$, $V_{GS} = 0V$, $T_J = +25$ °C
DYNAMIC CHARACTERISTICS (Note 12)						
Input Capacitance	C _{iss}		279	_	pF	101/1/
Output Capacitance	Coss		52	_	pF	$V_{DS} = 10V, V_{GS} = 0V$ -f = 1MHz
Reverse Transfer Capacitance	C _{rss}		29	_	pF	1 - 1101112
Total Gate Charge	Q_g		3.8	_	nC	V _{GS} = 4.5V
Gate-Source Charge	Q_{gs}	_	0.41	_	nC	V _{DS} = 10V
Gate-Drain Charge	Q_{gd}	_	0.56	_	nC	I _D = 2.4A
Turn-On Delay Time (Note 11)	t _{D(on)}	_	2.0	_	ns	
Turn-On Rise Time (Note 11)	t _r	_	3.2	_	ns	V _{DD} = 10V, V _{GS} = 4.5V
Turn-Off Delay Time (Note 11)	t _{D(off)}	_	12.7	_	ns	$I_D = 1.0A, R_G \cong 6.0\Omega$
Turn-Off Fall Time (Note 11)	t _f	_	6.2	_	ns	
Reverse Recovery Time	t _{rr}	_	6.6	_	ns	I _F = 1.24A, di/dt = 100A/μs,
Reverse Recovery Charge	Qrr		1.6		nC	T _J = +25℃

Notes:

^{10.} Measured under pulsed conditions. Pulse width ≤ 300µs; duty cycle ≤ 2%.
11. Switching characteristics are independent of operating junction temperature.
12. For design aid only, not subject to production testing.

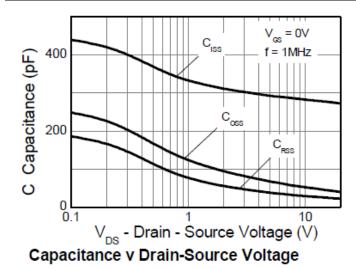


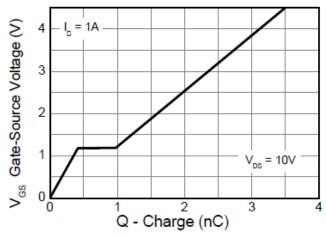
Typical Characteristics





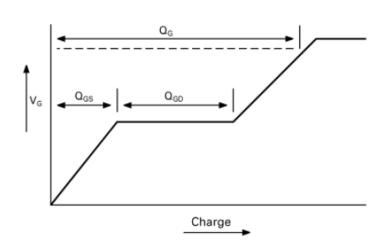
Typical Characteristics (continued)

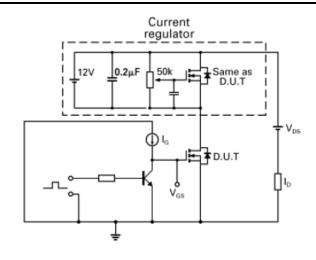




Gate-Source Voltage v Gate Charge

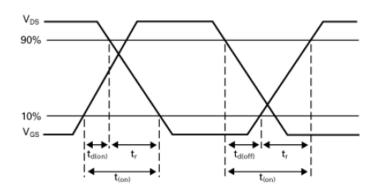
Test Circuits

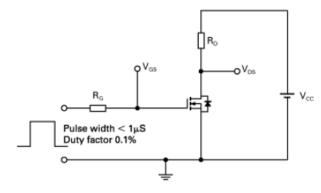




Basic gate charge waveform

Gate charge test circuit





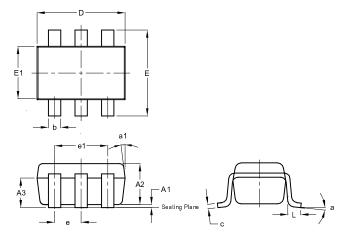
Switching time waveforms

Switching time test circuit



Package Outline Dimensions

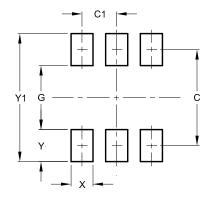
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



	SOT26						
Dim	Min	Тур					
A1	0.013	0.10	0.05				
A2	1.00	1.30	1.10				
A3	0.70	0.80	0.75				
b	0.35	0.50	0.38				
С	0.10	0.20	0.15				
D	2.90	3.10	3.00				
е	-	-	0.95				
e1	-	1	1.90				
Е	2.70	3.00	2.80				
E1	1.50	1.70	1.60				
L	0.35	0.55	0.40				
а	-	-	8°				
a1	-	-	7°				
All	All Dimensions in mm						

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.40
C1	0.95
G	1.60
Х	0.55
Y	0.80
Y1	3.20



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